

### **INCHANGE SEMICONDUCTOR**

## **Isc N-Channel MOSFET Transistor**

# IRF1310NL

D(2)

S(3)

pin 1, Gate 2, Drain

3, Source

2 3

### • FEATURES

- With To-262 package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

Switching applications

• ABSO	LUTE MAXIMUM RATINGS(Ta=25°C	TO-262 package			
SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>DSS</sub>	Drain-Source Voltage	100	V		
V <sub>GSS</sub>	Gate-Source Voltage	±20	V		
ID	Drain Current-ContinuousTc=25℃ Tc=100℃	42 30	А		
I <sub>DM</sub>	Drain Current-Single Pulsed	140	А	mm   DIM MIN MAX   A 4.37 4.77	
PD	Total Dissipation @Tc=25℃	160	W	A1 1.22 1.42   A2 2.47 2.87   b 0.70 0.97	
T <sub>ch</sub>	Max. Operating Junction Temperature	175	°C	b2 1.17 1.42 c 0.28 0.53 D 23.20 24.02 D1 8.38 8.90	
T <sub>stg</sub>	Storage Temperature	-55~175	°C	D2 6.00 -   E 9.90 10.39   E4 7.30 -   e 2.54BSC	
• THER	MAL CHARACTERISTICS	$\begin{array}{c} G & 1.25 \\ \hline G & 1.25 \\ \hline H2 & - & 1.31 \\ \hline L & 13.34 \\ \hline 14.10 \\ \end{array}$			
SYMBOL	PARAMETER	МАХ	UNIT	L1 3.30 4.06 L3 0.95 1.15	
Rth(ch-c)	Channel-to-case thermal resistance	0.95	°C/W		

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### ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	100			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =22A			36	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> =80V; V <sub>GS</sub> = 0V;Tj=125℃			25 250	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =22A, V <sub>GS</sub> = 0 V			1.3	V

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